

Properties of GaN seed layer using Ga(mDTC)₃ precursor

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Abstract- Tris (N,N-dimethyldithiocarbamate)-gallium(III) (Ga(mDTC)₃) is used as a precursor for formation of seed-layers in growth of gallium nitride (GaN) thin-film. GaN seed layers are formed on Al₂O₃ substrates by spin-coating method and nitridation in NH₃/N₂ ambient of reactor at 850°C. Structure of seed layers such as quality, surface morphology is examined by X-Ray Diffractometer, scanning electron microscope (SEM). Photoluminescence (PL) with He-Cd laser source is used to characterize band structure of seed-layers at room temperature.